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Kind regards,

Team Nexperia

PDTC144E series

NPN resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω

Rev. 9 — 15 November 2011

Product data sheet

1. Product profile

1.1 General description

NPN Resistor-Equipped Transistor (RET) family in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	Package	Package		PNP	Package	
	NXP JEITA JEDEC complement		complement	configuration		
PDTC144EE	SOT416	SC-75	-	PDTA144EE	ultra small	
PDTC144EM	SOT883	SC-101	-	PDTA144EM	leadless ultra small	
PDTC144ET	SOT23	-	TO-236AB	PDTA144ET	small	
PDTC144EU	SOT323	SC-70	-	PDTA144EU	very small	

1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

1.3 Applications

- Digital applications in automotive and industrial segments
- Control of IC inputs

- Cost-saving alternative for BC847/857 series in digital applications
- Switching loads

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
Io	output current		-	-	100	mA
R1	bias resistor 1 (input)		33	47	61	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	



Transparent

2. Pinning information

Table 3. **Pinning** Pin Simplified outline **Graphic symbol Description** SOT23; SOT323; SOT416 1 input (base) 3 2 GND (emitter) 3 output (collector) 2 006aaa144 sym007 **SOT883** 1 input (base) 2 GND (emitter) output (collector)

3. Ordering information

Table 4. Ordering information

Type number	Package	Package						
	Name	Description	Version					
PDTC144EE	SC-75	plastic surface-mounted package; 3 leads	SOT416					
PDTC144EM	SC-101	leadless ultra small plastic package; 3 solder lands; body 1.0 \times 0.6 \times 0.5 mm	SOT883					
PDTC144ET	-	plastic surface-mounted package; 3 leads	SOT23					
PDTC144EU	SC-70	plastic surface-mounted package; 3 leads	SOT323					

4. Marking

Table 5. Marking codes

3	
Type number	Marking code ^[1]
PDTC144EE	08
PDTC144EM	E7
PDTC144ET	*08
PDTC144EU	*08

[1] * = placeholder for manufacturing site code

5. Limiting values

Table 6. Limiting values

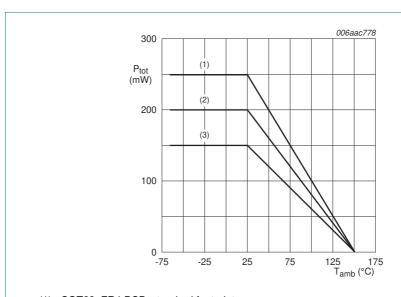
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	50	V
V_{CEO}	collector-emitter voltage	open base	-	50	V
V_{EBO}	emitter-base voltage	open collector	-	10	V
VI	input voltage				
	positive		-	+40	V
	negative		-	-10	V
Io	output current		-	100	mA
I _{CM}	peak collector current	$\begin{array}{l} \text{single pulse;} \\ t_p \leq 1 \text{ ms} \end{array}$	-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	PDTC144EE (SOT416)		[1][2]	150	mW
	PDTC144EM (SOT883)		[2][3]	250	mW
	PDTC144ET (SOT23)		[1] -	250	mW
	PDTC144EU (SOT323)		[1] -	200	mW
T _j	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[2] Reflow soldering is the only recommended soldering method.

^[3] Device mounted on an FR4 PCB with 70 μm copper strip line, standard footprint.



- (1) SOT23; FR4 PCB, standard footprint SOT883; FR4 PCB with 70 μm copper strip line, standard footprint
- (2) SOT323; FR4 PCB, standard footprint
- (3) SOT416; FR4 PCB, standard footprint

Fig 1. Power derating curves

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j\text{-}a)}$	thermal resistance from junction to ambient	in free air				
	PDTC144EE (SOT416)		[1][2]	-	830	K/W
	PDTC144EM (SOT883)		[2][3]	-	500	K/W
	PDTC144ET (SOT23)		[1] -	-	500	K/W
	PDTC144EU (SOT323)		[1] -	-	625	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Reflow soldering is the only recommended soldering method.
- [3] Device mounted on an FR4 PCB with 70 μm copper strip line, standard footprint.

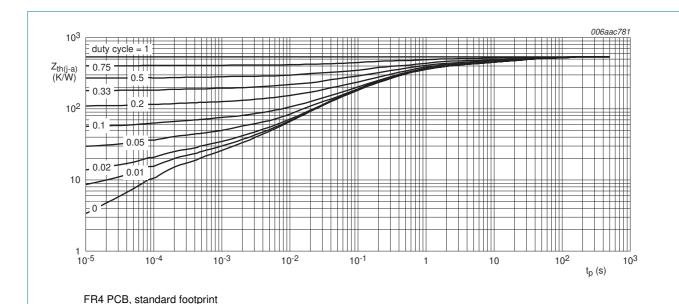
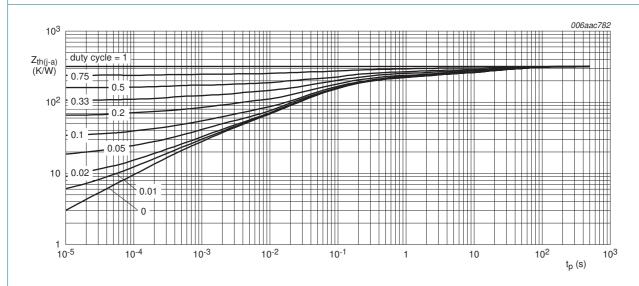


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTC144EE (SOT416); typical values



FR4 PCB, 70 µm copper strip line

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTC144EM (SOT883); typical values

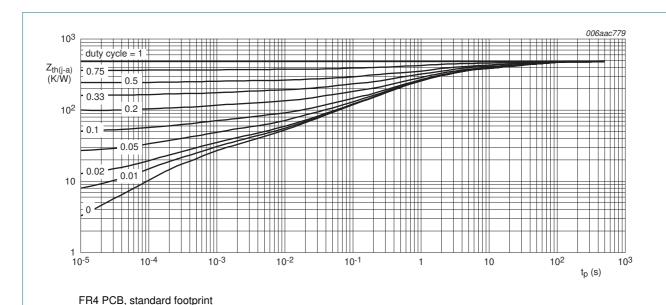


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTC144ET (SOT23); typical values

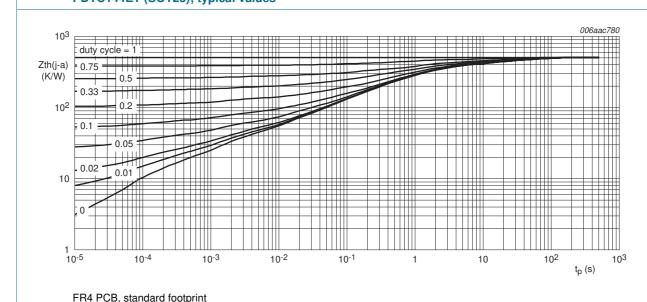


Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTC144EU (SOT323); typical values

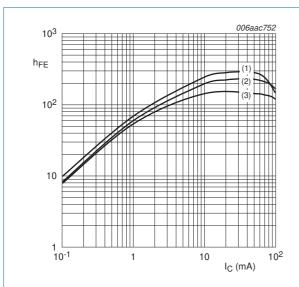
7. Characteristics

Table 8. Characteristics

T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	тур Тур	Max	Unit
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I _{CEO}		$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}$	-	-	1	μΑ
cut-off cu	cut-off current	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	5	μА
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$	-	-	90	μΑ
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 5 \text{ mA}$	80	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	-	150	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5 \text{ V}; I_{C} = 100 \mu\text{A}$	-	1.2	8.0	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 2 \text{ mA}$	3	1.6	-	V
R1	bias resistor 1 (input)		33	47	61	kΩ
R2/R1	bias resistor ratio		8.0	1	1.2	
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ $f = 1 \text{ MHz}$	-	-	2.5	pF
f _T	transition frequency	$V_{CE} = 5 \text{ V; } I_{C} = 10 \text{ mA;}$ f = 100 MHz	<u>[1]</u> _	230	-	MHz

^[1] Characteristics of built-in transistor



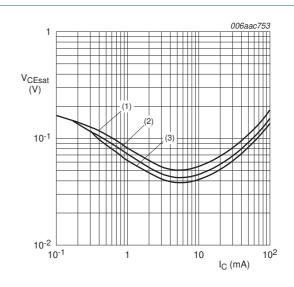
$$V_{CE} = 5 \text{ V}$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 6. DC current gain as a function of collector current; typical values



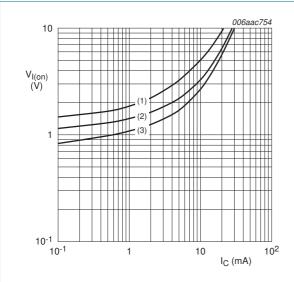
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values



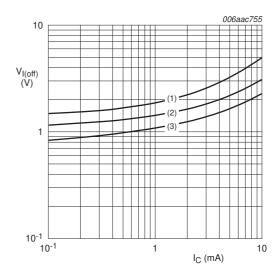
$$V_{CE} = 0.3 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 8. On-state input voltage as a function of collector current; typical values



$$V_{CE} = 5 V$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 9. Off-state input voltage as a function of collector current; typical values

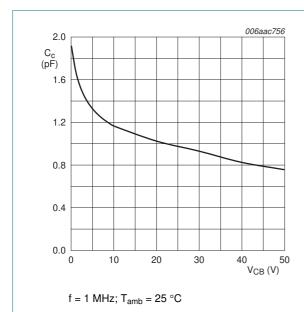


Fig 10. Collector capacitance as a function of collector-base voltage; typical values

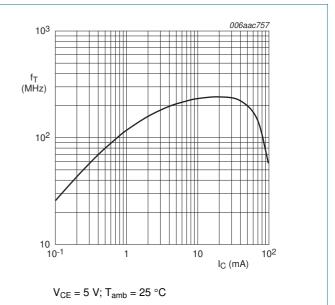


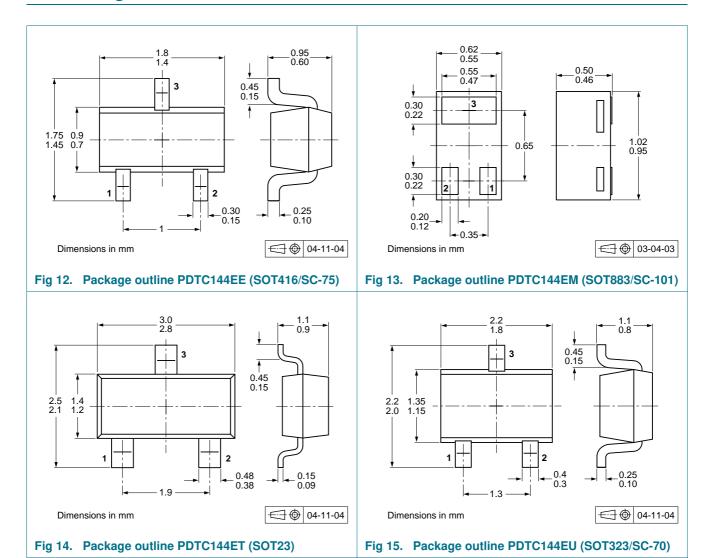
Fig 11. Transition frequency as a function of collector current; typical values of built-in transistor

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing	Packing quantity		
			3000	5000	10000	
PDTC144EE	SOT416	4 mm pitch, 8 mm tape and reel	-115	-	-135	
PDTC144EM	SOT883	2 mm pitch, 8 mm tape and reel	-	-	-315	
PDTC144ET	SOT23	4 mm pitch, 8 mm tape and reel	-215	-	-235	
PDTC144EU	SOT323	4 mm pitch, 8 mm tape and reel	-115	-	-135	

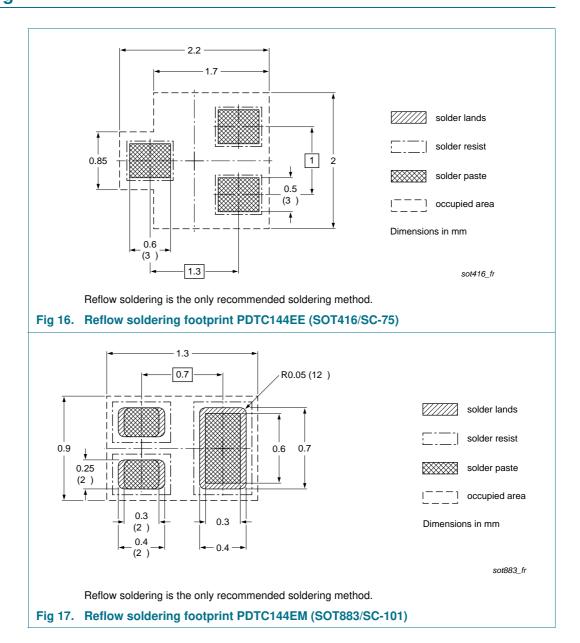
[1] For further information and the availability of packing methods, see Section 14.

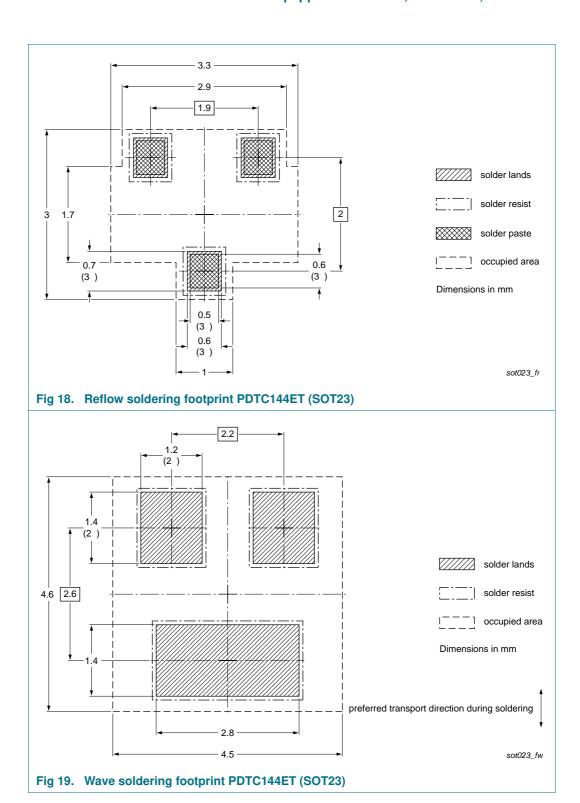
PDTC144E_SER

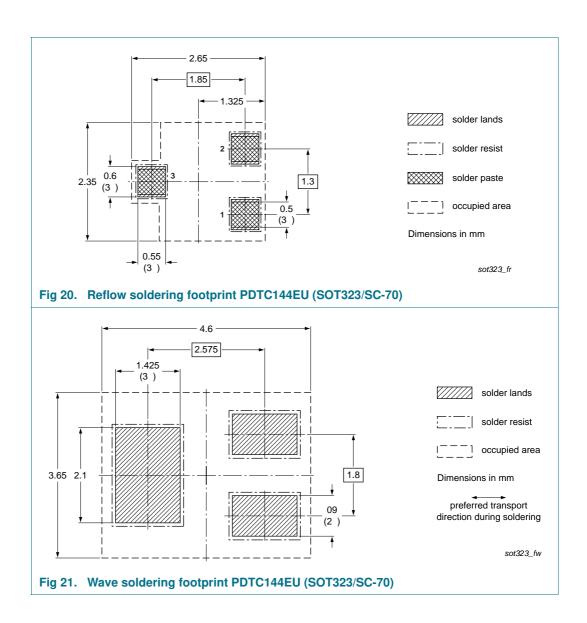
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11. Soldering







12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes			
PDTC144E_SER v.9	20111115	Product data sheet	-	PDTC144E_SERIES v.8			
Modifications:		f this document has been re NXP Semiconductors.	designed to comply w	ith the new identity			
	 Legal texts h 	ave been adapted to the ne	w company name whe	re appropriate.			
	 Type number 	 Type numbers PDTC144EEF, PDTC144EK and PDTC144ES removed. 					
	 Section 1 "Pr 	oduct profile": updated					
	Section 3 "Or	rdering information": update	d				
	Section 4 "Magnetic street stree	Section 4 "Marking": updated					
	 Figure 1 to 1 	• Figure 1 to 11: added					
	 Section 6 "Th 	nermal characteristics": upda	ated				
	• Table 8 "Cha	racteristics": V _{i(on)} redefined	to $V_{I(on)}$ on-state input	voltage, $V_{i(off)}$ redefined			
	to $V_{I(off)}$ off-st	ate input voltage, I _{CEO} upda	ited, f _T added				
	 Section 8 "Te 	est information": added					
	 Section 9 "Pa 	ackage outline": superseded	by minimized package	e outline drawings			
	 Section 10 "F 	Packing information": added					
	Section 11 "S	Soldering": added					
	 Section 13 "L 	<u>egal information"</u> : updated					
PDTC144E_SERIES v.8	20040817	Product data sheet	-	PDTC144E_SERIES v.7			
PDTC144E_SERIES v.7	20040323	Product specification	-	PDTC144E_SERIES v.6			
PDTC144E_SERIES v.6	20030414	Product specification	-	-			

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions"
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PDTC144E_SER

PDTC144E series

NPN resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

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14. Contact information

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For sales office addresses, please send an email to: salesaddresses@nxp.com

PDTC144E series

NPN resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω

15. Contents

1	Product profile
1.1	General description 1
1.2	Features and benefits
1.3	Applications
1.4	Quick reference data 1
2	Pinning information 2
3	Ordering information 2
4	Marking 2
5	Limiting values 3
6	Thermal characteristics 4
7	Characteristics 7
8	Test information 9
8.1	Quality information 9
9	Package outline
10	Packing information 10
11	Soldering 11
12	Revision history 14
13	Legal information
13.1	Data sheet status
13.2	Definitions
13.3	Disclaimers
13.4	Trademarks16
14	Contact information 16
15	Contents 17

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